

AO7402

N-Channel Enhancement Mode Field Effect Transistor

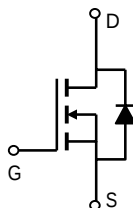
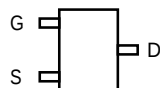
General Description

The AO7402 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 1.8V, in the small SOT323 footprint. It can be used for a wide variety of applications, including load switching, low current inverters and low current DC-DC converters. *Standard Product AO7402 is Pb-free (meets ROHS & Sony 259 specifications). AO7402L is a Green Product ordering option. AO7402 and AO7402L are electrically identical.*

Features

$V_{DS} (V) = 20V$
 $I_D = 1.6 A (V_{GS} = 4.5V)$
 $R_{DS(ON)} < 90m\Omega (V_{GS} = 4.5V)$
 $R_{DS(ON)} < 105m\Omega (V_{GS} = 2.5V)$
 $R_{DS(ON)} < 130m\Omega (V_{GS} = 1.8V)$

SC-70
(SOT-323)
Top View



Absolute Maximum Ratings $T_A=25^\circ C$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	± 8	V
Continuous Drain Current ^A	I_D	1.6	A
	$T_A=70^\circ C$	1.2	
Pulsed Drain Current ^B	I_{DM}	10	
Power Dissipation ^A	P_D	0.35	W
	$T_A=70^\circ C$	0.22	
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^\circ C$

Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	300	360	$^\circ C/W$
Maximum Junction-to-Ambient ^A		340	425	$^\circ C/W$
Maximum Junction-to-Lead ^C	$R_{\theta JL}$	280	320	$^\circ C/W$

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV _{DSS}	Drain-Source Breakdown Voltage	I _D =250μA, V _{GS} =0V	20			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =16V, V _{GS} =0V T _J =55°C			1 5	μA
I _{GSS}	Gate-Body leakage current	V _{DS} =0V, V _{GS} =±8V			100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	0.4	0.55	0.8	V
I _{D(ON)}	On state drain current	V _{GS} =4.5V, V _{DS} =5V	10			A
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =4.5V, I _D =1.6A T _J =125°C		75 106	90 130	mΩ
		V _{GS} =2.5V, I _D =1.5A		86	105	mΩ
		V _{GS} =1.8V, I _D =1.4A		103	130	mΩ
g _{FS}	Forward Transconductance	V _{DS} =5V, I _D =1.6A		5.5		S
V _{SD}	Diode Forward Voltage	I _S =1A, V _{GS} =0V		0.69	1	V
I _S	Maximum Body-Diode Continuous Current				0.5	A
DYNAMIC PARAMETERS						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =10V, f=1MHz		458		pF
C _{oss}	Output Capacitance			76		pF
C _{rss}	Reverse Transfer Capacitance			54		pF
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, f=1MHz		3		Ω
SWITCHING PARAMETERS						
Q _g	Total Gate Charge	V _{GS} =4.5V, V _{DS} =10V, I _D =1.6A		6.05		nC
Q _{gs}	Gate Source Charge			0.7		nC
Q _{gd}	Gate Drain Charge			1.45		nC
t _{D(on)}	Turn-On DelayTime	V _{GS} =5V, V _{DS} =10V, R _L =6.25Ω, R _{GEN} =6Ω		7.3		ns
t _r	Turn-On Rise Time			5.6		ns
t _{D(off)}	Turn-Off DelayTime			40		ns
t _f	Turn-Off Fall Time			11		ns
t _{rr}	Body Diode Reverse Recovery Time	I _F =1.6A, dI/dt=100A/μs		12.2		ns
Q _{rr}	Body Diode Reverse Recovery Charge	I _F =1.6A, dI/dt=100A/μs		3.23		nC

A: The value of R_{θJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The value in any given application depends on the user's specific board design. The current rating is based on the t_s ≤ 10s thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C: The R_{θJA} is the sum of the thermal impedance from junction to lead R_{θJL} and lead to ambient.

D: The static characteristics in Figures 1 to 6, 12, 14 are obtained using 80μs pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The SOA curve provides a single pulse rating.

Rev 3: Sept 2005

THIS PRODUCT HAS BEEN DESIGNED AND QUALIFIED FOR THE CONSUMER MARKET. APPLICATIONS OR USES AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS ARE NOT AUTHORIZED. AOS DOES NOT ASSUME ANY LIABILITY ARISING OUT OF SUCH APPLICATIONS OR USES OF ITS PRODUCTS. AOS RESERVES THE RIGHT TO IMPROVE PRODUCT DESIGN, FUNCTIONS AND RELIABILITY WITHOUT NOTICE.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

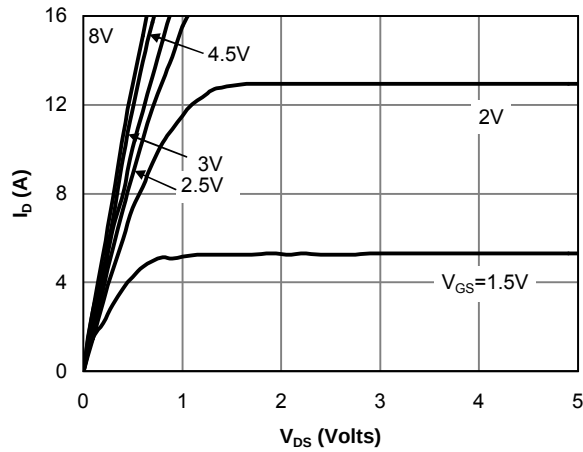


Fig 1: On-Region Characteristics

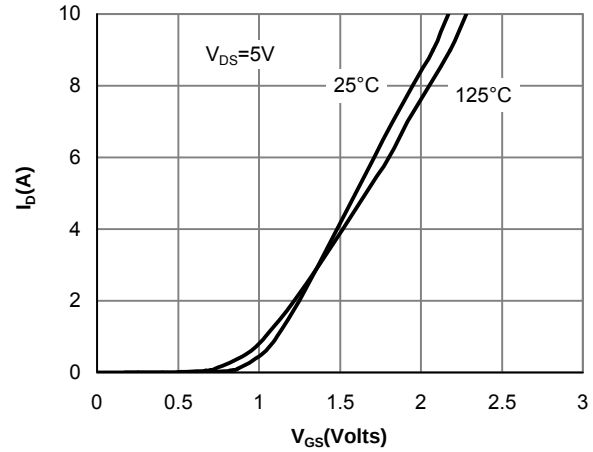


Figure 2: Transfer Characteristics

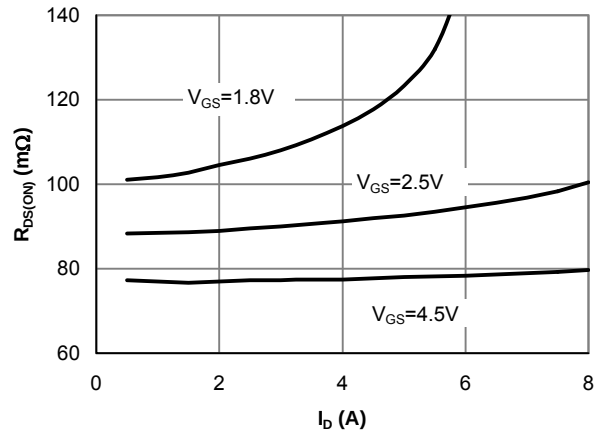


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

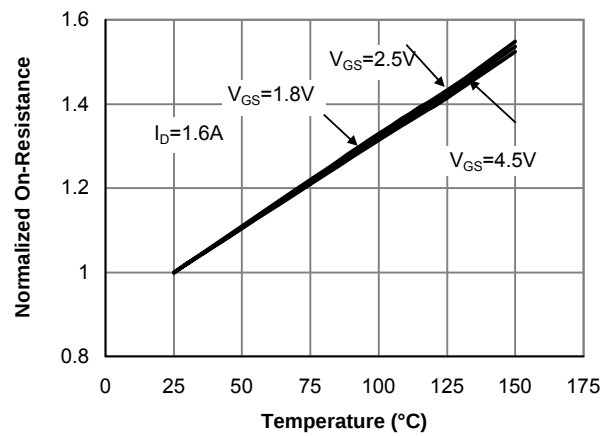


Figure 4: On-Resistance vs. Junction Temperature

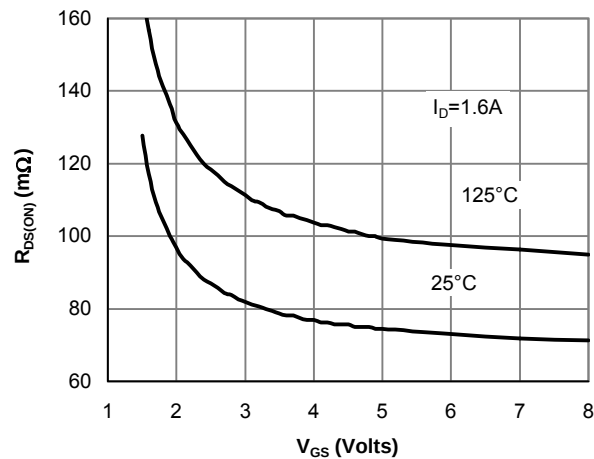


Figure 5: On-Resistance vs. Gate-Source Voltage

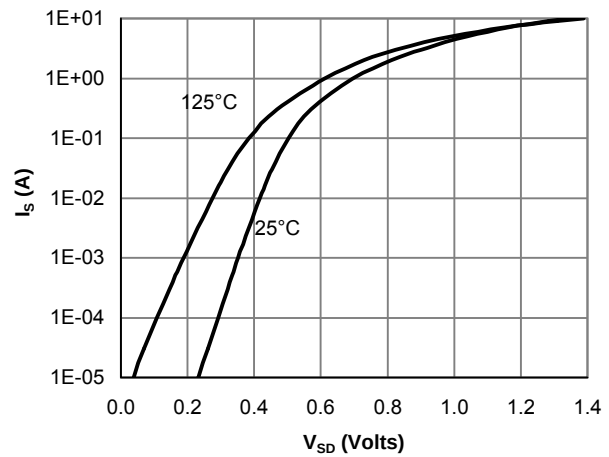


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

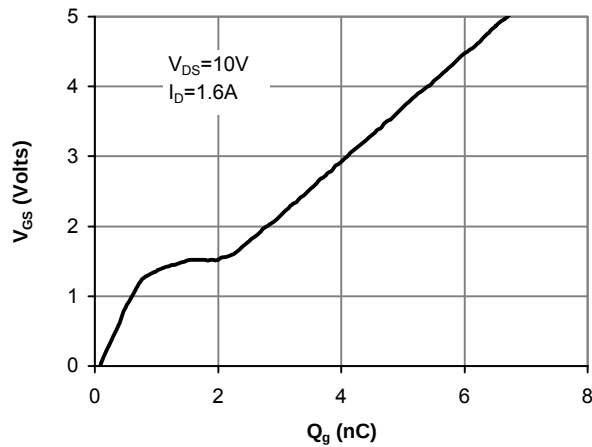


Figure 7: Gate-Charge Characteristics

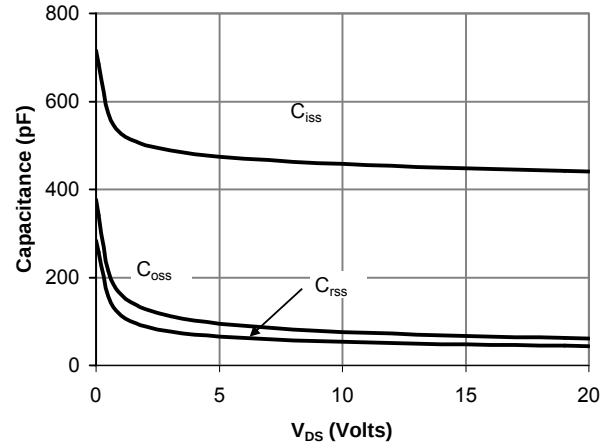


Figure 8: Capacitance Characteristics

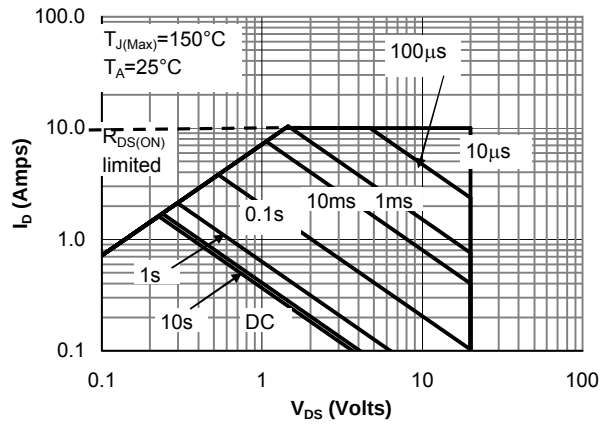


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

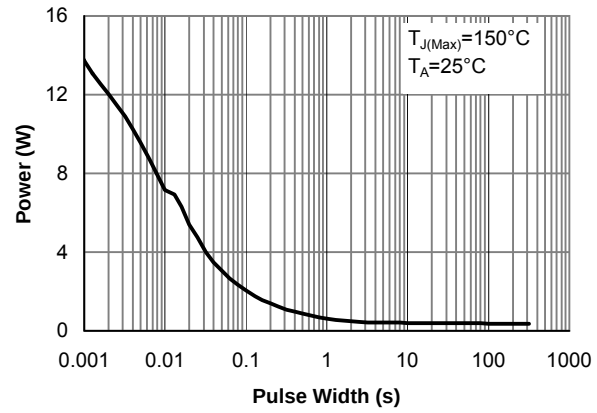


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

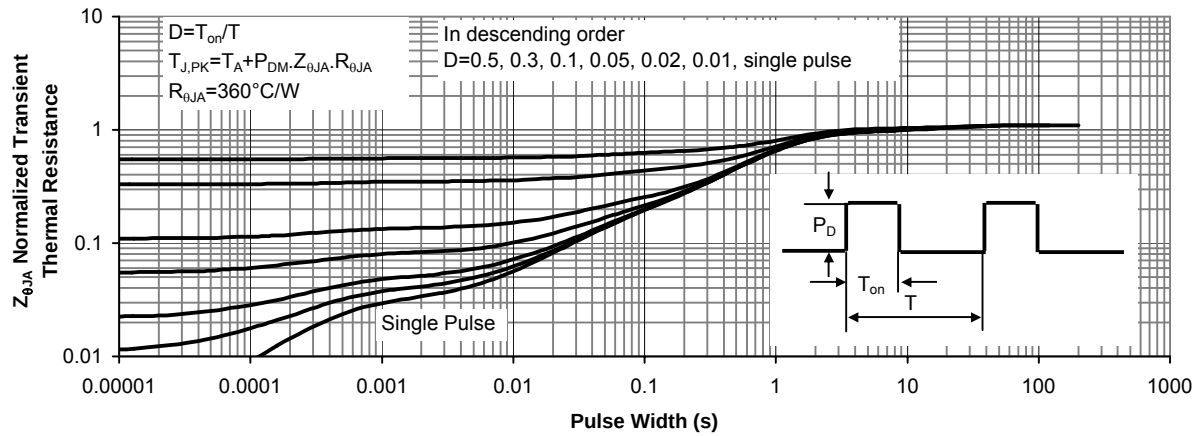


Figure 11: Normalized Maximum Transient Thermal Impedance